

Features

- Freq: 2~12GHz
- Slope: 3 dB
- Insertion Loss: 0.8dB@12GHz
- Chip Size: 0.88mm×0.56mm×0.1mm

General Description

The HG115JB is a GaAs pHEMT equalizer. Covering 2 to 12 GHz, this equalizer offers very high slope of 3 dB and extremely low insertion loss of 0.8dB@12GHz. Input and output VSWR are 1.1/1.1.

Electrical Specifications($T_A=25^\circ\text{C}$)

Parameter	Min.	Typ.	Max.
Frequency Range(GHz)	2~12		
Input VSWR	-	1.1	-
Output VSWR	-	1.1	-
Insertion Loss(dB)	-	0.8~3.8	-
Slope(dB)	-	3	-

Absolute Maximum Ratings

RF Input Power	+27dBm
Operating Temperature	-55°C~125°C
Storage Temperature	-65°C~150°C

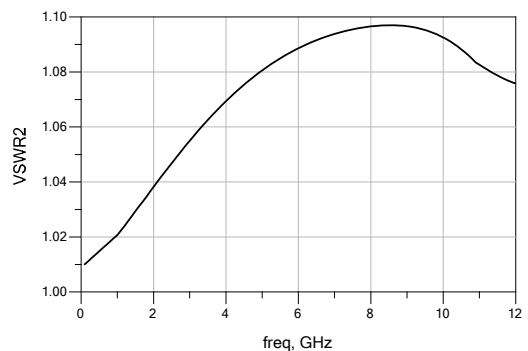
Insertion Loss



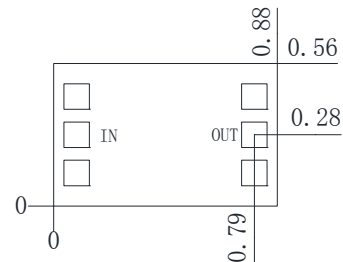
Input VSWR



Output VSWR



Outline Drawing (mm)



Notes:

- The chip should be stored in a dry and nitrogen environment, and used in a clean environment.
- GaAs material is brittle, can not touch the surface of the chip, must be careful when using.
- The chip is welding with conductive adhesive or alloy (alloy temperature should not exceed 300°C, and no more than 30 sec.), and should make it fully grounded.
- The chip microwave port and substrate gap is not exceeding 0.05mm, with $\Phi 25\mu\text{m}$ double gold wire bonding, suggested length of gold wire 250~400 μm .
- Chip microwave port without DC blocking capacitor.
- The chip is sensitive to static electricity, and should be protected against static electricity during storage and use.